

## Product Summary

BV <sub>DSS</sub>	R <sub>DS(on)</sub> Max	I <sub>D</sub> Max T <sub>A</sub> = +25°C
30V	11mΩ @ V <sub>GS</sub> = 10V	10.5A
	15mΩ @ V <sub>GS</sub> = 4.5V	9.2A

## Features and Benefits

- Low R<sub>DS(on)</sub> – Ensures On State Losses Are Minimized
- 100% Unclamped Inductive Switching, Test in Production – Ensures More Reliable And Robust End Application
- Small Form Factor Thermally Efficient Package Enables Higher Density End Products
- Occupies Just 33% of The Board Area Occupied by SO-8 Enabling Smaller End Product
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **The DMG7430LFGQ is suitable for automotive applications requiring specific change control; this part is AEC-Q101 qualified, PPAP capable, and manufactured in IATF 16949 certified facilities.**  
<https://www.diodes.com/quality/product-definitions/>

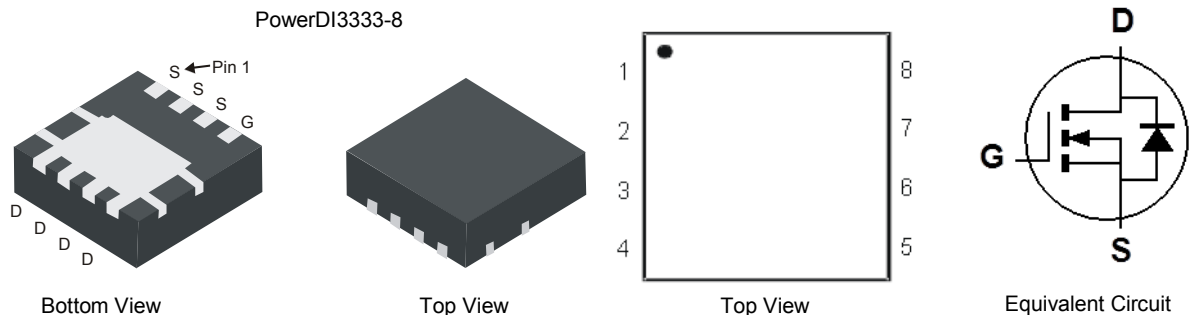
## Description and Applications

This MOSFET is designed to meet the stringent requirements of automotive applications. It is qualified to AEC-Q101, supported by a PPAP and is ideal for use in:

- Motor Control
- Power Management Functions
- DC-DC Converters

## Mechanical Data

- Case: PowerDI<sup>®</sup> 3333-8
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 3 per J-STD-020
- Terminal Connections Indicator: See Diagram
- Terminals: Finish—Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 @3
- Weight: 0.072 grams (Approximate)

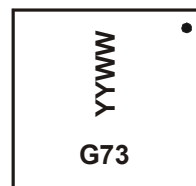


## Ordering Information (Note 4)

Part Number	Case	Packaging
DMG7430LFGQ-7	PowerDI3333-8	2000/Tape & Reel
DMG7430LFGQ-13	PowerDI3333-8	3000/Tape & Reel

- Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
  2. See <https://www.diodes.com/quality/lead-free/> for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
  3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
  4. For packaging details, go to our website at <https://www.diodes.com/design/support/packaging/diodes-packaging/>.

## Marking Information



- G73 = Product Type Marking Code
- YYWW = Date Code Marking
- YY = Last Two Digits of Year (ex: 21 = 2021)
- WW = Week Code (01 to 53)

**Maximum Ratings** (@  $T_A = +25^\circ\text{C}$ , unless otherwise specified.)

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			$V_{DSS}$	30	V
Gate-Source Voltage			$V_{GSS}$	$\pm 20$	V
Continuous Drain Current (Note 6) $V_{GS} = 10\text{V}$	Steady State	$T_A = +25^\circ\text{C}$ $T_A = +70^\circ\text{C}$	$I_D$	10.5 8.5	A
	$t < 10\text{s}$	$T_A = +25^\circ\text{C}$ $T_A = +70^\circ\text{C}$	$I_D$	14 11	A
Pulsed Drain Current (10 $\mu\text{s}$ Pulse, Duty Cycle = 1%)			$I_{DM}$	90	A
Maximum Continuous Body Diode Forward Current (Note 6)			$I_S$	3.0	A
Avalanche Current (Note 7) $L = 0.1\text{mH}$			$I_{AR}$	22	A
Repetitive Avalanche Energy (Note 7) $L = 0.1\text{mH}$			$E_{AR}$	24	mJ

**Thermal Characteristics** (@  $T_A = +25^\circ\text{C}$ , unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 5)	Steady State	$P_D$	0.9	W
	$t < 10\text{s}$		1.5	
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	$R_{\theta JA}$	142	$^\circ\text{C/W}$
	$t < 10\text{s}$		78	
Total Power Dissipation (Note 6)	Steady State	$P_D$	2.2	W
	$t < 10\text{s}$		3.5	
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	$R_{\theta JA}$	59	$^\circ\text{C/W}$
	$t < 10\text{s}$		33	
Thermal Resistance, Junction to Case (Note 6)		$R_{\theta JC}$	11	$^\circ\text{C}$
Operating and Storage Temperature Range		$T_J, T_{STG}$	-55 to +150	$^\circ\text{C}$

- Notes: 5. Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.  
6. Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.  
7.  $I_{AR}$  and  $E_{AR}$  ratings are based on low frequency and duty cycles to keep  $T_J = +25^\circ\text{C}$ .

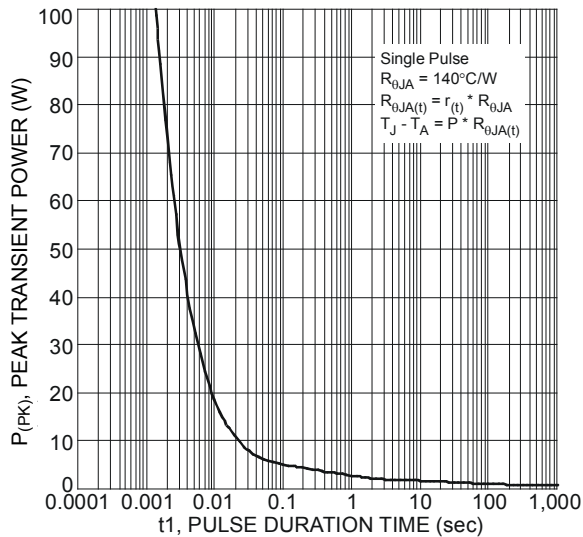


Fig. 1 Single Pulse Maximum Power Dissipation

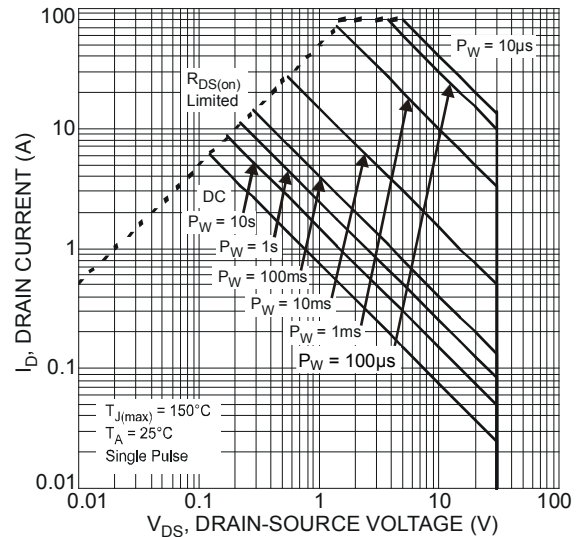


Fig. 2 SOA, Safe Operation Area

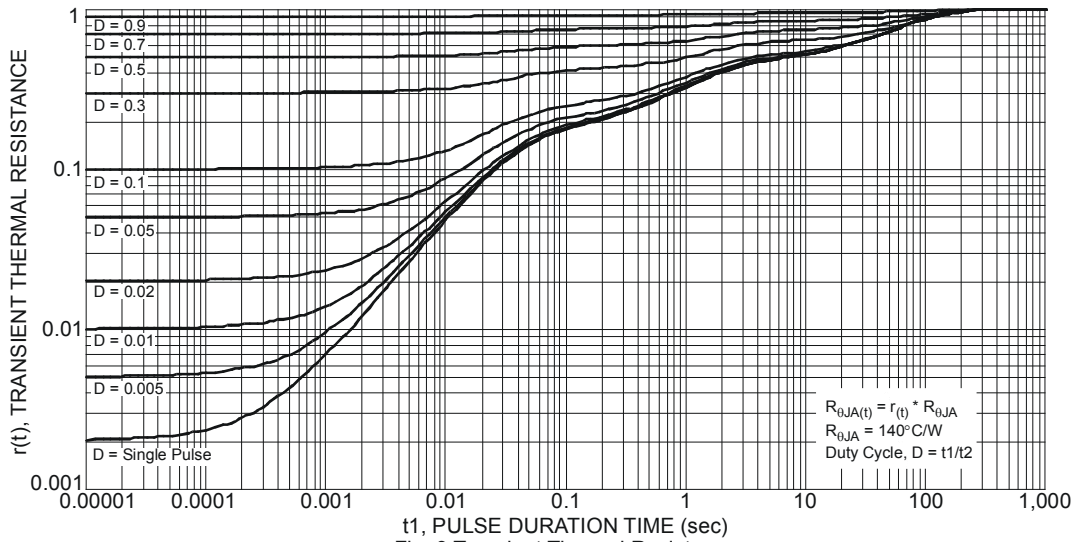


Fig. 3 Transient Thermal Resistance

**Electrical Characteristics** (@ T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
<b>OFF CHARACTERISTICS (Note 8)</b>						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	30	—	—	V	V <sub>GS</sub> = 0V, I <sub>D</sub> = 250μA
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	—	—	1	μA	V <sub>DS</sub> = 30V, V <sub>GS</sub> = 0V
Gate-Source Leakage	I <sub>GSS</sub>	—	—	±100	nA	V <sub>GS</sub> = ±20V, V <sub>DS</sub> = 0V
<b>ON CHARACTERISTICS (Note 8)</b>						
Gate Threshold Voltage	V <sub>GS(th)</sub>	1.4	—	2.5	V	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250μA
Static Drain-Source On-Resistance	R <sub>DS(on)</sub>	—	7	11	mΩ	V <sub>GS</sub> = 10V, I <sub>D</sub> = 20A
		—	11	15		V <sub>GS</sub> = 4.5V, I <sub>D</sub> = 20A
Forward Transfer Admittance	Y <sub>fs</sub>	—	74	—	S	V <sub>DS</sub> = 5V, I <sub>D</sub> = 20A
Diode Forward Voltage	V <sub>SD</sub>	—	0.75	1.0	V	V <sub>GS</sub> = 0V, I <sub>S</sub> = 1A
<b>DYNAMIC CHARACTERISTICS (Note 9)</b>						
Input Capacitance	C <sub>iss</sub>	—	1281	—	pF	V <sub>DS</sub> = 15V, V <sub>GS</sub> = 0V, f = 1.0MHz
Output Capacitance	C <sub>oss</sub>	—	145	—	pF	
Reverse Transfer Capacitance	C <sub>rss</sub>	—	125	—	pF	
Gate Resistance	R <sub>g</sub>	—	1.2	—	Ω	V <sub>DS</sub> = 0V, V <sub>GS</sub> = 0V, f = 1.0MHz
Total Gate Charge (V <sub>GS</sub> = 4.5V)	Q <sub>g</sub>	—	12.5	—	nC	V <sub>DS</sub> = 15V, I <sub>D</sub> = 12A
Total Gate Charge (V <sub>GS</sub> = 10V)	Q <sub>g</sub>	—	26.7	—	nC	
Gate-Source Charge	Q <sub>gs</sub>	—	3.6	—	nC	
Gate-Drain Charge	Q <sub>gd</sub>	—	4.4	—	nC	
Turn-On Delay Time	t <sub>D(on)</sub>	—	5.2	—	ns	V <sub>DD</sub> = 15V, V <sub>GS</sub> = 10V, R <sub>L</sub> = 1.25Ω, R <sub>G</sub> = 3Ω
Turn-On Rise Time	t <sub>R</sub>	—	21.2	—	ns	
Turn-Off Delay Time	t <sub>D(off)</sub>	—	22.3	—	ns	
Turn-Off Fall Time	t <sub>F</sub>	—	5.1	—	ns	
Reverse Recovery Time	t <sub>RR</sub>	—	8.5	—	ns	I <sub>F</sub> = 12A, di/dt = 500A/μs
Reverse Recovery Charge	Q <sub>RR</sub>	—	7.0	—	nC	I <sub>F</sub> = 12A, di/dt = 500A/μs

Notes: 8. Short duration pulse test used to minimize self-heating effect.  
9. Guaranteed by design. Not subject to product testing.

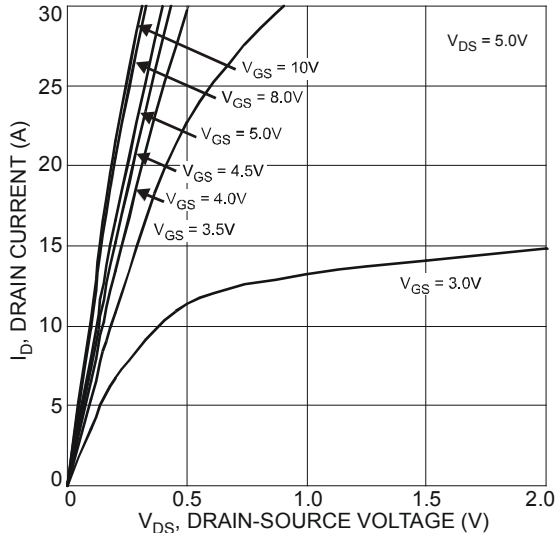


Fig. 4 Typical Output Characteristic

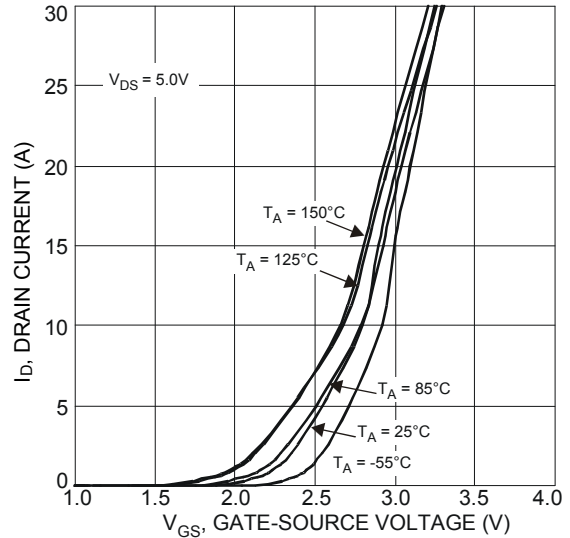


Fig. 5 Typical Transfer Characteristics

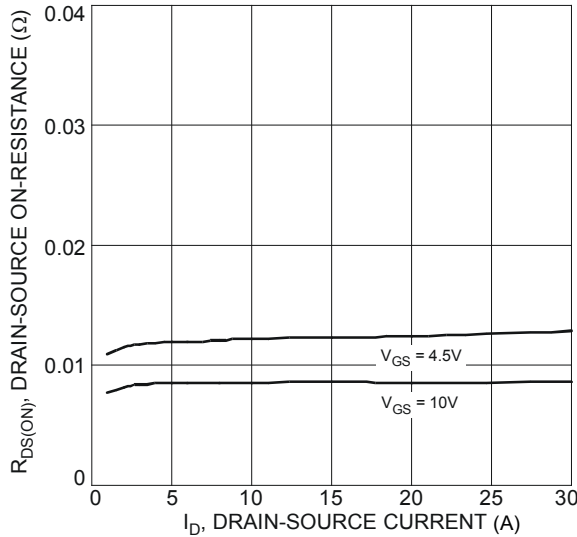


Fig. 6 Typical On-Resistance vs. Drain Current and Gate Voltage

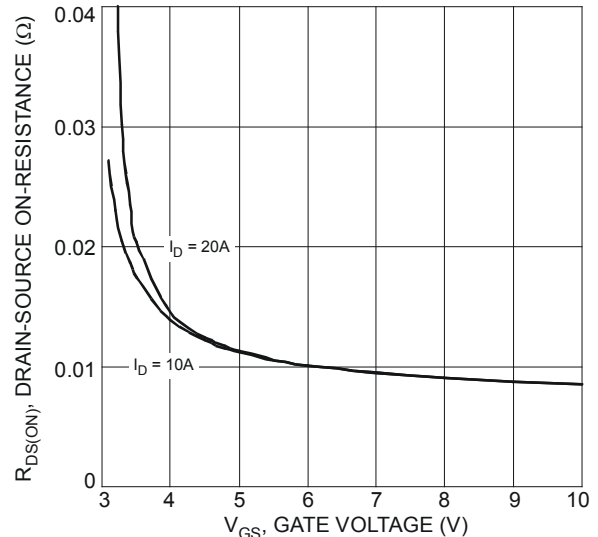


Fig. 7 Typical On-Resistance vs. Gate Voltage

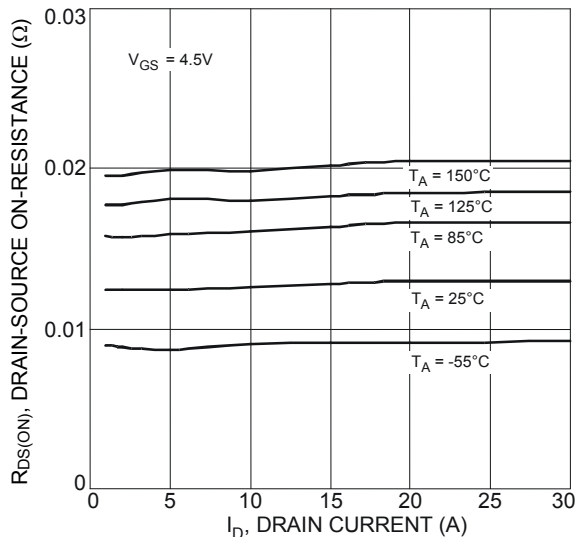


Fig. 8 Typical On-Resistance vs. Drain Current and Temperature

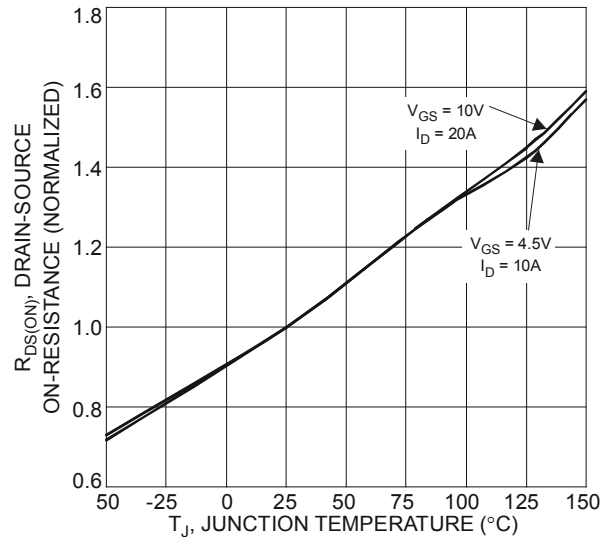


Fig. 9 On-Resistance Variation with Temperature

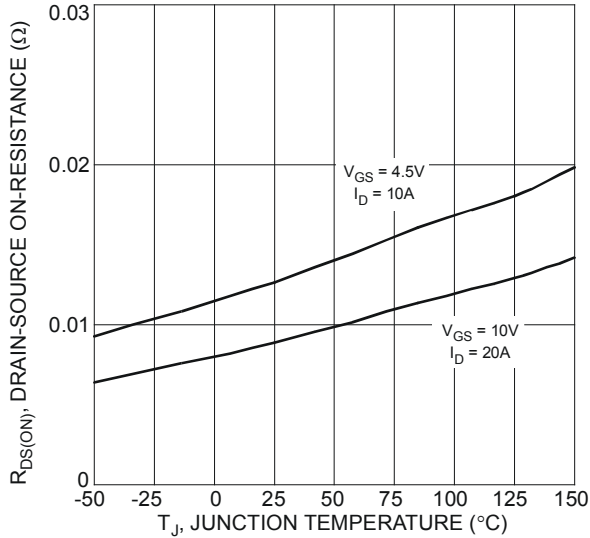


Fig. 10 On-Resistance Variation with Temperature

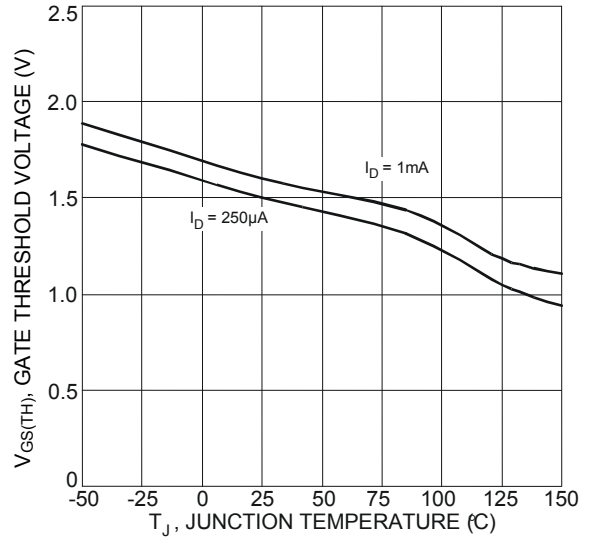


Fig. 11 Gate Threshold Variation vs. Junction Temperature

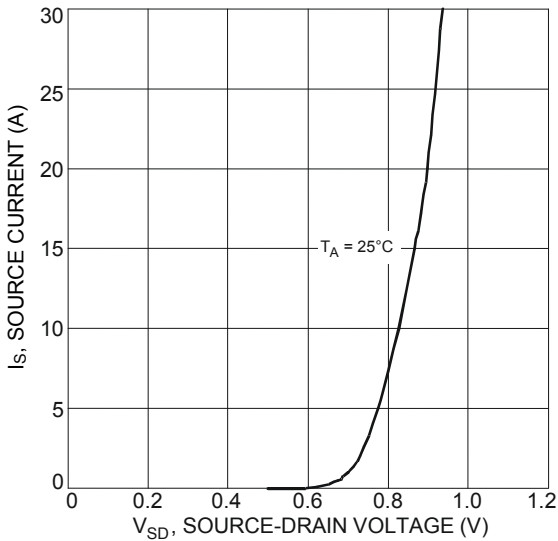


Fig. 12 Diode Forward Voltage vs. Current

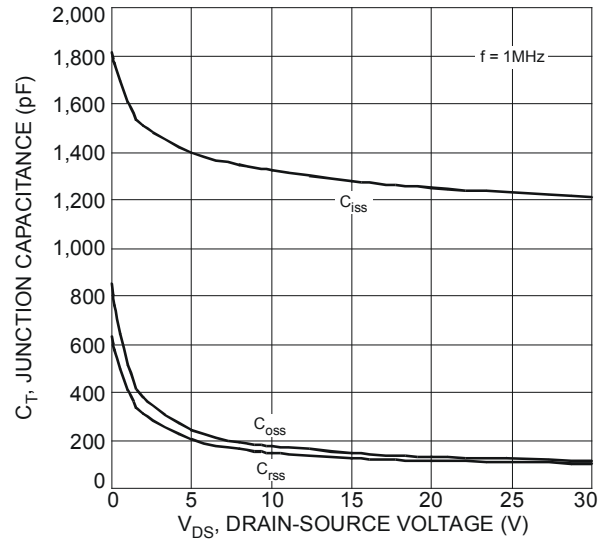


Fig. 13 Typical Junction Capacitance

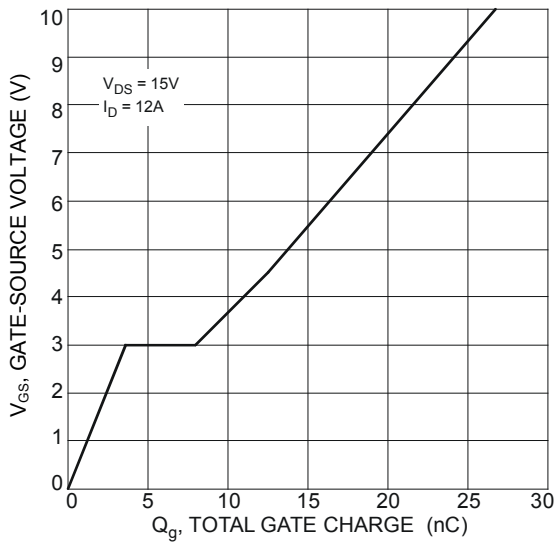
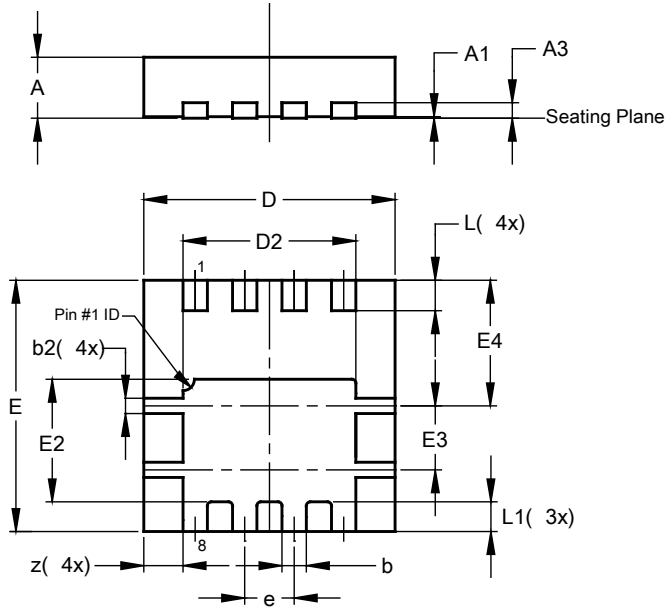


Fig. 14 Gate Charge

**Package Outline Dimensions**

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

**PowerDI3333-8**

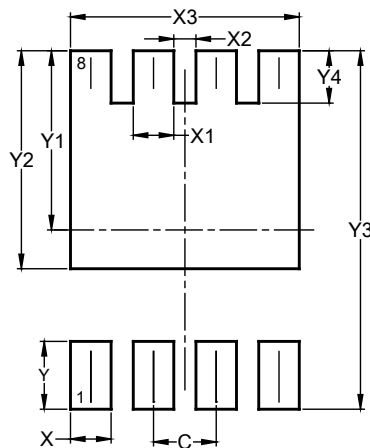


PowerDI3333-8			
Dim	Min	Max	Typ
A	0.75	0.85	0.80
A1	0.00	0.05	0.02
A3	-	-	0.203
b	0.27	0.37	0.32
b2	0.15	0.25	0.20
D	3.25	3.35	3.30
D2	2.22	2.32	2.27
E	3.25	3.35	3.30
E2	1.56	1.66	1.61
E3	0.79	0.89	0.84
E4	1.60	1.70	1.65
e	-	-	0.65
L	0.35	0.45	0.40
L1	-	-	0.39
z	-	-	0.515
<b>All Dimensions in mm</b>			

**Suggested Pad Layout**

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

**PowerDI3333-8**



Dimensions	Value (in mm)
C	0.650
X	0.420
X1	0.420
X2	0.230
X3	2.370
Y	0.700
Y1	1.850
Y2	2.250
Y3	3.700
Y4	0.540

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